Euijoon Yoon

List of Publications by Year in Descending Order

Source: https://exaly.com/author-pdf/3258388/euijoon-yoon-publications-by-year.pdf
Version: 2024-04-09

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.
The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

147 papers	2,534 citations	27 h-index	46 g-index
165 ext. papers	2,865 ext. citations	5.1 avg, IF	4.68 L-index

#	Paper	IF	Citations
147	Strain relaxation and dislocation annihilation in compositionally graded □(AlxGa1-x)2O3 layer for high voltage □Ga2O3 power devices. *Acta Materialia*, **2021**, 221, 117423	8.4	3
146	Crystalline silicon nanoparticle formation by tailored plasma irradiation: self-structurization, nucleation and growth acceleration, and size control. *Nanoscale*, **2021**, 13, 10356-10364	7.7	2
145	A discrete core-shell-like micro-light-emitting diode array grown on sapphire nano-membranes. *Scientific Reports*, **2020**, 10, 7506	4.9	5
144	Direct observation and catalytic role of mediator atom in 2D materials. *Science Advances*, **2020**, 6, eaba4942	14.3	5
143	Strain relaxation effects on TE-polarized light emission and in-plane polarization ratio in c-plane ultraviolet AlGaN/AlN quantum well structures. *Physica E: Low-Dimensional Systems and Nanostructures*, **2020**, 120, 114112	3	
142	The influence of hydrogen concentration in amorphous carbon films on mechanical properties and fluorine penetration: a density functional theory and molecular dynamics study.. *RSC Advances*, **2020**, 10, 6822-6830	3.7	4
141	Temperature-Dependent Polarized Photoluminescence from c-plane InGaN/GaN Multiple Quantum Wells Grown on Stripe-Shaped Cavity-Engineered Sapphire Substrate. *Physica Status Solidi (B): Basic Research*, **2020**, 257, 1900526	1.3	1
140	Thermodynamic insights into interfacial interactions in TiN/amorphous Al2O3 heterostructures: ab initio molecular dynamics and first principles investigation. *Inorganic Chemistry Frontiers*, **2020**, 7, 4347-4356	6.8	0
139	Effects of the flux-controlled cation off-stoichiometry in SrRuO3 grown by molecular beam epitaxy on its physical and electrical properties. *Materials Letters*, **2020**, 281, 128375	3.3	1
138	Analysis of surface adsorption kinetics of SiH4 and Si2H6 for deposition of a hydrogenated silicon thin film using intermediate pressure SiH4 plasmas. *Applied Surface Science*, **2019**, 496, 143728	6.7	7
137	Atomic Structure and Dynamics of Epitaxial Platinum Bilayers on Graphene. *ACS Nano*, **2019**, 13, 12162-12170	13.7	12
136	Atomic Scale Imaging of Reversible Ring Cyclization in Graphene Nanoconstrictions. *ACS Nano*, **2019**, 13, 2379-2388	16.7	2
135	Highly polarized photoluminescence from c-plane InGaN/GaN multiple quantum wells on stripe-shaped cavity-engineered sapphire substrate. *Scientific Reports*, **2019**, 9, 8282	4.9	6
134	Effects of nitrogen doping in amorphous carbon layers on the diffusion of fluorine atoms: A first-principles study. *Journal of Applied Physics*, **2019**, 125, 155701	2.5	8
133	Monolithic lntegratIon of GaAs//InGaAs photodetectors for multicolor detection **2019**,		2
132	First principles investigation on energetics, structure, and mechanical properties of amorphous carbon films doped with B, N, and Cl. *Scientific Reports*, **2019**, 9, 18961	4.9	3
131	Fabrication of Less Bowed Light-Emitting Diodes on Sapphire Substrates with a SiO2 Thin Film on Their Back Sides. *Journal of the Korean Physical Society*, **2019**, 75, 480-484	0.6	1

130	Monolithic integration of visible GaAs and near-infrared InGaAs for multicolor photodetectors by using high-throughput epitaxial lift-off toward high-resolution imaging systems. *Scientific Reports*, **2019**, 9, 18661	4.9	15
129	Epitaxial lateral overgrowth of GaN on nano-cavity patterned sapphire substrates. *Journal of Crystal Growth*, **2019**, 507, 103-108	1.6	5
128	Flaw-Containing Alumina Hollow Nanostructures Have Ultrahigh Fracture Strength To Be Incorporated into High-Efficiency GaN Light-Emitting Diodes. *Nano Letters*, **2018**, 18, 1323-1330	11.5	6
127	Solid-phase epitaxy of a cavity-shaped amorphous alumina nanomembrane structure on a sapphire substrate. *Journal of Crystal Growth*, **2018**, 498, 130-136	1.6	8
126	Room temperature operation of mid-infrared InAsSb based photovoltaic detectors with an InAlSb barrier layer grown on GaAs substrates. *Optics Express*, **2018**, 26, 6249-6259	3.3	9
125	Microstructured void gratings for outcoupling deep-trap guided modes. *Optics Express*, **2018**, 26, A450-A461	3.3	4
124	Epitaxial growth of single-crystalline AlN layer on Si(111) by DC magnetron sputtering at room temperature. *Japanese Journal of Applied Physics*, **2018**, 57, 060306	1.4	9
123	Linearly polarized photoluminescence of anisotropically strained c-plane GaN layers on stripe-shaped cavity-engineered sapphire substrate. *Applied Physics Letters*, **2018**, 112, 212102	3.4	4
122	Single-Crystalline Nanobelts Composed of Transition Metal Ditellurides. *Advanced Materials*, **2018**, 30, e1707260	24	15
121	Effects of H and N treatment for BH dosing process on TiN surfaces during atomic layer deposition: an study.. *RSC Advances*, **2018**, 8, 21164-21173	3.7	3
120	Overall reaction mechanism for a full atomic layer deposition cycle of W films on TiN surfaces: first-principles study.. *RSC Advances*, **2018**, 8, 39039-39046	3.7	3
119	Solid-Phase Epitaxial Growth of an Alumina Layer Having a Stacking-Mismatched Domain Structure of the Intermediate Phase. *ACS Applied Materials & Interfaces*, **2018**, 10, 41487-41496	9.5	3
118	Surface structurization and control of CuS particle size by discharge mode of inductively coupled plasma and vapor-phase sulfurization. *Plasma Sources Science and Technology*, **2018**, 27, 114002	3.5	4
117	Improved performance of AlGaN-based deep ultraviolet light-emitting diodes with nano-patterned AlN/sapphire substrates. *Applied Physics Letters*, **2017**, 110, 191103	3.4	63
116	Heterogeneously integrated high-performance GaAs single-junction solar cells on copper. *Journal of the Korean Physical Society*, **2017**, 70, 693-698	0.6	3
115	Point defects in turbostratic stacked bilayer graphene. *Nanoscale*, **2017**, 9, 13725-13730	7.7	8
114	Gaseous Nanocarving-Mediated Carbon Framework with Spontaneous Metal Assembly for Structure-Tunable Metal/Carbon Nanofibers. *Advanced Materials*, **2017**, 29, 1702958	24	10
113	Enhanced Thermal Conductivity of the Underfill Materials Using Insulated Core/shell Filler Particles for High Performance Flip Chip Applications **2017**,		2

112	Dissociation reaction of B2H6 on TiN surfaces during atomic layer deposition: first-principles study. *RSC Advances*, **2017**, 7, 55750-55755	3.7	9
111	In Situ Atomic Level Dynamics of Heterogeneous Nucleation and Growth of Graphene from Inorganic Nanoparticle Seeds. *ACS Nano*, **2016**, 10, 9397-9410	16.7	8
110	Suppression of surface leakage current in InSb photodiode by ZnS passivation. *International Journal of Nanotechnology*, **2016**, 13, 392	1.5	3
109	Ultra-high-throughput Production of III-V/Si Wafer for Electronic and Photonic Applications. *Scientific Reports*, **2016**, 6, 20610	4.9	66
108	Atomic Structure and Spectroscopy of Single Metal (Cr, V) Substitutional Dopants in Monolayer MoS. *ACS Nano*, **2016**, 10, 10227-10236	16.7	77
107	Elongated Silicon-Carbon Bonds at Graphene Edges. *ACS Nano*, **2016**, 10, 142-9	16.7	15
106	An ultra-thin compliant sapphire membrane for the growth of less strained, less defective GaN. *Journal of Crystal Growth*, **2016**, 441, 52-57	1.6	7
105	Control of Crack Formation for the Fabrication of Crack-Free and Self-Isolated High-Efficiency Gallium Arsenide Photovoltaic Cells on Silicon Substrate. *IEEE Journal of Photovoltaics*, **2016**, 6, 1031-1035	3.7	14
104	Microstructured Air Cavities as High-Index Contrast Substrates with Strong Diffraction for Light-Emitting Diodes. *Nano Letters*, **2016**, 16, 3301-8	11.5	33
103	Detailed Atomic Reconstruction of Extended Line Defects in Monolayer MoS2. *ACS Nano*, **2016**, 10, 5419-30	16.7	115
102	Rotating Anisotropic Crystalline Silicon Nanoclusters in Graphene. *ACS Nano*, **2015**, 9, 9497-506	16.7	13
101	A new growth method of semi-insulating GaN layer for HEMT structure by eliminating degenerate layer at GaN/sapphire interface. *Current Applied Physics*, **2015**, 15, S11-S15	2.6	1
100	Atomic Level Distributed Strain within Graphene Divacancies from Bond Rotations. *ACS Nano*, **2015**, 9, 8599-608	16.7	20
99	Atomic Structure of Graphene Subnanometer Pores. *ACS Nano*, **2015**, 9, 11599-607	16.7	56
98	Incorporation of air-cavity into sapphire substrate and its effect on GaN growth and optical properties. *Journal of Crystal Growth*, **2015**, 430, 41-45	1.6	20
97	Thermally Induced Dynamics of Dislocations in Graphene at Atomic Resolution. *ACS Nano*, **2015**, 9, 10066-75	16.7	27
96	Partial Dislocations in Graphene and Their Atomic Level Migration Dynamics. *Nano Letters*, **2015**, 15, 5950-5	11.5	33
95	Reduction in threading dislocation density in ge epitaxial layers grown on Si(001) substrates by using rapid thermal annealing. *Journal of the Korean Physical Society*, **2015**, 67, 1646-1650	0.6	1

94	Growth of High Quality Ge Layer on Silica Nano-Spheres Integrated Ge/Si Template Using UHV-CVD. *ECS Journal of Solid State Science and Technology*, **2015**, 4, P83-P85	2	1
93	Infrared photoreflectance investigation of resonant levels and band edge structure in InSb. *Optics Letters*, **2015**, 40, 5295-8	3	6
92	Effects of growth temperature on surface morphology of InP grown on patterned Si(0 0 1) substrates. *Journal of Crystal Growth*, **2015**, 416, 113-117	1.6	9
91	Investigation of leakage current paths in n-GaN by conductive atomic force microscopy. *Applied Physics Letters*, **2014**, 104, 102101	3.4	49
90	Effects of TMSb overpressure on InSb surface morphology for InSb epitaxial growth using low pressure metalorganic chemical vapor deposition. *Journal of Crystal Growth*, **2014**, 401, 518-522	1.6	3
89	Hydrogen-free graphene edges. *Nature Communications*, **2014**, 5, 3040	17.4	63
88	The role of the bridging atom in stabilizing odd numbered graphene vacancies. *Nano Letters*, **2014**, 14, 3972-80	11.5	36
87	Stability and dynamics of the tetravacancy in graphene. *Nano Letters*, **2014**, 14, 1634-42	11.5	57
86	Advanced Si solid phase crystallization for vertical channel in vertical NANDs. *APL Materials*, **2014**, 2, 076106	5.7	1
85	Selective growth of N-polar InN through an in situ AlN mask on a sapphire substrate. *Applied Physics Letters*, **2014**, 104, 032108	3.4	11
84	Analysis of failure of C-V characteristics of MIS structure with SiO2 passivation layer deposited on InSb substrate via Raman spectroscopy. *Materials Research Society Symposia Proceedings*, **2014**, 1670, 25		
83	Strained Quantum Rings. *Nanoscience and Technology*, **2014**, 331-352	0.6	
82	Formation and development of dislocation in graphene. *Applied Physics Letters*, **2013**, 102, 021603	3.4	28
81	Growth of GaN layer with preserved nano-columnar low temperature GaN buffer to reduce the wafer bowing. *Thin Solid Films*, **2013**, 546, 118-123	2.2	4
80	Characterization of deep levels in GaInP on Ge and Ge-on-Si substrates by photoluminescence and cathodoluminescence. *Journal of Crystal Growth*, **2013**, 370, 168-172	1.6	4
79	Less strained and more efficient GaN light-emitting diodes with embedded silica hollow nanospheres. *Scientific Reports*, **2013**, 3, 3201	4.9	33
78	Strong carrier localization and diminished quantum-confined Stark effect in ultra-thin high-indium-content InGaN quantum wells with violet light emission. *Applied Physics Letters*, **2013**, 103, 222104	3.4	4
77	Improved crystal quality of a-plane GaN with high- temperature 3-dimensional GaN buffer layers deposited by using metal-organic chemical vapor deposition. *Journal of the Korean Physical Society*, **2012**, 60, 1297-1300	0.6	

76	Catalyst-free growth of InN nanorods by metal-organic chemical vapor deposition. *Physica Status Solidi (A) Applications and Materials Science*, **2012**, 209, 50-55	1.6	4
75	Fabrication of a-plane InN nanostructures on patterned a-plane GaN template by ECR-MBE. *Physica Status Solidi (A) Applications and Materials Science*, **2012**, 209, 447-450	1.6	2
74	Growth of Less Bowed GaN Epitaxial Layers on Sapphire Substrates by Formation of Low-Temperature GaN Buffer Layer with Columnar Microstructure. *Japanese Journal of Applied Physics*, **2012**, 51, 01AF01	1.4	
73	Growth of Less Bowed GaN Epitaxial Layers on Sapphire Substrates by Formation of Low-Temperature GaN Buffer Layer with Columnar Microstructure. *Japanese Journal of Applied Physics*, **2012**, 51, 01AF01	1.4	1
72	Investigation of InN mole fraction fluctuation in InGaN films grown by RF-MBE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1499-1502		2
71	Growth mechanism of highly uniform InAs/GaAs quantum dot with periodic arsine interruption by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **2011**, 110, 044302	2.5	3
70	Growth of Si-doped GaInP on Ge-on-Si substrates and its photoluminescence characteristics. *Applied Physics Letters*, **2011**, 99, 091904	3.4	9
69	Dynamics and stability of divacancy defects in graphene. *Physical Review B*, **2011**, 84,	3.3	80
68	Anomalous strain profiles and electronic structures of a GaAs-capped InAs/In0.53Ga0.47As quantum ring. *Journal of Applied Physics*, **2011**, 109, 103701	2.5	9
67	Effects of r-plane Sapphire Substrate Tilt Angles on the Growth Behavior of Nonpolar a-plane GaN. *Journal of the Korean Physical Society*, **2011**, 58, 906-910	0.6	2
66	The role of pentagon□heptagon pair defect in carbon nanotube: The center of vacancy reconstruction. *Applied Physics Letters*, **2010**, 97, 093106	3.4	14
65	Ultraviolet stimulated emission in periodically polarity-inverted ZnO structures at room temperature. *Applied Physics Letters*, **2010**, 97, 171101	3.4	1
64	Reconstruction and evaporation at graphene nanoribbon edges. *Physical Review B*, **2010**, 81,	3.3	53
63	Characteristics of blue and ultraviolet light-emitting diodes with current density and temperature. *Electronic Materials Letters*, **2010**, 6, 51-53	2.9	11
62	The effects of low temperature buffer layer on the growth of pure Ge on Si(001). *Thin Solid Films*, **2010**, 518, 6496-6499	2.2	23
61	MOCVD growth of GaN layer on InN interlayer and relaxation of residual strain. *Thin Solid Films*, **2010**, 518, 6365-6368	2.2	7
60	Competitive growth mechanisms of InAs quantum dots on InxGa1 □xAs layer during post growth interruption. *Thin Solid Films*, **2010**, 518, 6361-6364	2.2	1
59	Microstructural Investigation of Bilayer Growth of In- and Ga-Rich InGaN Grown by Chemical Vapor Deposition. *Journal of Electronic Materials*, **2009**, 38, 518-522	1.9	4

58	High quality Ge epitaxial layers on Si by ultrahigh vacuum chemical vapor deposition. *Thin Solid Films*, **2009**, 517, 3990-3994	2.2	12
57	Enhancement of optical properties of InAs quantum dots grown by using periodic arsine interruption. *Thin Solid Films*, **2009**, 517, 3963-3966	2.2	3
56	Effect of dimethylhydrazine on p-type conductivity of as-grown Mg-doped GaN. *Physica Status Solidi - Rapid Research Letters*, **2009**, 3, 52-54	2.5	
55	Study of UV excited white light-emitting diodes for optimization of luminous efficiency and color rendering index. *Physica Status Solidi - Rapid Research Letters*, **2009**, 3, 34-36	2.5	5
54	Anomalous strain relaxation and light-hole character enhancement in GaAs capped InAs/In0.53Ga0.47As quantum ring. *Physica Status Solidi - Rapid Research Letters*, **2009**, 3, 76-78	2.5	8
53	Improved Emission Efficiency in InGaN Light-Emitting Diodes Using Reverse Bias in Pulsed Voltage Operation. *IEEE Photonics Technology Letters*, **2008**, 20, 1190-1192	2.2	1
52	Optical and microstructural studies of atomically flat ultrathin In-rich InGaN□GaN multiple quantum wells. *Journal of Applied Physics*, **2008**, 103, 063509	2.5	28
51	Violet-light spontaneous and stimulated emission from ultrathin In-rich InGaN/GaN multiple quantum wells grown by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2008**, 93, 161905	3.4	5
50	The formation of pentagon-heptagon pair defect by the reconstruction of vacancy defects in carbon nanotube. *Applied Physics Letters*, **2008**, 92, 043104	3.4	33
49	Compositional analysis of In-rich InGaN layers grown on GaN templates by metalorganic chemical vapor deposition. *Journal of Crystal Growth*, **2008**, 310, 3004-3008	1.6	18
48	In situ monitoring of the growth procedure of InAs layer by spectral reflectance. *Journal of Crystal Growth*, **2007**, 298, 50-53	1.6	1
47	Thermodynamic study of AlGaN composition grown by metalorganic chemical vapor deposition. *Journal of Crystal Growth*, **2007**, 298, 367-371	1.6	4
46	Growth behavior and optical properties of In-rich InGaN quantum dots by metal-organic chemical vapor deposition. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 112-115		1
45	Complete suppression of large InAs island formation on GaAs by metal organic chemical vapor deposition with periodic AsH3 interruption. *Applied Physics Letters*, **2007**, 90, 033105	3.4	15
44	Formation of carbon nanotube semiconductor-metal intramolecular junctions by self-assembly of vacancy defects. *Physical Review B*, **2007**, 76,	3.3	30
43	Optical gain in InGaN□GaN quantum well structures with embedded AlGaN □layer. *Applied Physics Letters*, **2007**, 90, 023508	3.4	74
42	Diffusion of adatom in the selective epitaxial growth of Si(100): A molecular dynamics study. *Applied Physics Letters*, **2006**, 88, 231909	3.4	0
41	In-rich InGaN□GaN quantum wells grown by metal-organic chemical vapor deposition. *Journal of Applied Physics*, **2006**, 99, 044906	2.5	17

40	Vacancy defects and the formation of local haeckelite structures in graphene from tight-binding molecular dynamics. *Physical Review B*, **2006**, 74,	3.3	77
39	Diffusion, coalescence, and reconstruction of vacancy defects in graphene layers. *Physical Review Letters*, **2005**, 95, 205501	7.4	416
38	The emission wavelength tuning of InAs/InP quantum dots with thin GaAs, InGaAs, InP capping layers by MOCVD. *Physica E: Low-Dimensional Systems and Nanostructures*, **2005**, 26, 169-173	3	2
37	Simulation and fabrication of highly efficient InGaN-based LEDs with corrugated interface substrate. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 2874-2877		40
36	Measuring the junction temperature of III-nitride light emitting diodes using electro-luminescence shift. *Physica Status Solidi (A) Applications and Materials Science*, **2005**, 202, 1869-1873	1.6	39
35	Room temperature near-ultraviolet emission from In-rich InGaN□GaN multiple quantum wells. *Applied Physics Letters*, **2005**, 86, 192105	3.4	25
34	Effects of thin GaAs insertion layer on InAs□InGaAs)□InP(001) quantum dots grown by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2005**, 86, 223110	3.4	7
33	Growth of Nitride Quantum Dots **2005**, 95-131		
32	Comparison of the Strain-modified Band Gap Energies of Truncated and Untruncated InAs Quantum Dots in GaAs Matrix at Varying Inter-dot Spacings. *Journal of the Physical Society of Japan*, **2004**, 73, 3378-3383	1.5	1
31	Isotropic/anisotropic growth behavior and faceting morphology of Si epitaxial layer selectively grown by cold wall ultrahigh vacuum chemical vapor deposition. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2004**, 22, 275		7
30	Microscopic study on the behavior of the {311} facet in the selective epitaxial growth of Si(100). *Applied Physics Letters*, **2004**, 85, 4624-4626	3.4	2
29	The formation of cubic GaNAs phase during the growth of thin GaNAs epilayers on GaN at low temperatures by metalorganic chemical vapor deposition. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 2462-2465		2
28	Growth of In-rich InGaN/GaN quantum dots by metalorganic chemical vapor deposition. *Journal of Crystal Growth*, **2004**, 269, 95-99	1.6	24
27	Aspect ratio dependent strains in InAs/InP quantum dots measured by synchrotron radiation x-ray diffraction. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2003**, 21, 183		2
26	Si adatom diffusion on Si (100) surface in selective epitaxial growth of Si. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2003**, 21, 2388		9
25	Arsenic incorporation and growth mode of GaNAs grown by low-pressure metal-organic chemical vapor deposition. *Journal of Crystal Growth*, **2003**, 248, 437-440	1.6	9
24	Real time in situ monitoring of stacked InAs/InP quantum dots by spectral reflectance. *Journal of Crystal Growth*, **2003**, 248, 201-205	1.6	7
23	Growth of GaN epitaxial layers on sapphire with preheated ammonia and their structural and optoelectronic properties. *Current Applied Physics*, **2003**, 3, 351-354	2.6	7

22	Optical properties of InAs/InP quantum dot stack grown by metalorganic chemical vapor deposition. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 1347-1350		
21	The growth of In-rich InGaN/GaN single quantum wells by metalorganic chemical vapor deposition. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 2834-2837		7
20	Effect of growth interruption on In-rich InGaN/GaN single quantum well structures. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 2830-2833		9
19	Comparison of 500nm InGaN/GaN QW Emission Properties Induced by Piezoelectric Field Effect and Phase Separation. *Materials Research Society Symposia Proceedings*, **2000**, 639, 11191		
18	Effects of growth interruption on the evolution of InAs/InP self-assembled quantum dots. *Journal of Electronic Materials*, **2000**, 29, 535-541	1.9	13
17	Highly (200)-oriented Pt films on SiO2/Si substrates by seed selection through amorphization and controlled grain growth. *Journal of Materials Research*, **1999**, 14, 634-637	2.5	21
16	Analysis of P adsorption and desorption on the (001) InP surface using surface photoabsorption. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1999**, 17, 2663-2667	2.9	7
15	Quantitative analysis of the compositional profile of a single quantum well by grazing incidence x-ray reflectivity and photoluminescence. *Applied Physics Letters*, **1999**, 74, 2152-2154	3.4	2
14	Changes in Preferred Orientation of Pt Thin Films Deposited by dc Magnetron Sputtering Using Ar/O2 Gas Mixtures. *Journal of Materials Research*, **1999**, 14, 1255-1260	2.5	25
13	Shape change of InAs self-assembled quantum dots induced by As/P exchange reaction. *Thin Solid Films*, **1999**, 357, 81-84	2.2	9
12	Effect of Hydrogen on GaN Growth by Remote Plasma-Enhanced Metal-Organic Chemical Vapor Deposition. *Physica Status Solidi A*, **1999**, 176, 337-342		4
11	Effects of As/P exchange reaction on the formation of InAs/InP quantum dots. *Applied Physics Letters*, **1999**, 74, 2029-2031	3.4	104
10	Low temperature photoluminescence characteristics of Zn-doped InP grown by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **1998**, 83, 2261-2265	2.5	30
9	Changes in the growth mode of low temperature GaN buffer layers with nitrogen plasma nitridation of sapphire substrates. *Applied Physics Letters*, **1997**, 71, 1228-1230	3.4	32
8	(100) Oriented Platinum thin Films Deposited by Dc Magnetron Sputtering On SiO2/Si Substrates. *Materials Research Society Symposia Proceedings*, **1996**, 441, 335		3
7	Characterization of Platinum films Deposited by a Two-Step Magnetron Sputtering on SiO2/Si Substrates. *Materials Research Society Symposia Proceedings*, **1996**, 441, 341		7
6	Stress of Platinum Thin Films Deposited by Dc Magnetron Sputtering Using Argon/Oxygen Gas Mixture. *Materials Research Society Symposia Proceedings*, **1996**, 441, 427		1
5	Nitrogen Plasma Pretreatment of Sapphire Substrates for the GaN Buffer Growth by Remote Plasma Enhanced MOCVD. *Materials Research Society Symposia Proceedings*, **1996**, 449, 53		2

4	Low-Temperature Metalorganic Chemical Vapor Deposition of Gallium Nitride on (0001) Sapphire Substrates Using a Remote RF Nitrogen Plasma. *Materials Research Society Symposia Proceedings*, **1996**, 449, 95		6
3	Noncontact minority carrier lifetime measurement of Si and SiGe epilayers prepared by ultrahigh vacuum electron cyclotron resonance chemical vapor deposition. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1996**, 14, 1033-1036	2.9	4
2	Electrically driven mid-submicrometre pixelation of InGaN micro-light-emitting diode displays for augmented-reality glasses. *Nature Photonics*,	33.9	22
1	Selective Area Growth of Single-Crystalline Alpha-Gallium Oxide on a Sapphire Nanomembrane by Mist Chemical Vapor Deposition. *ACS Applied Electronic Materials*,	4	3